

DESCRIPTION

This is a Silicon Phototransistor designed for applications requiring medium gain and a wide viewing angle.

FEATURES

- Medium Gain, typically 500 Hfe
- Sensitivity range 400-1000 nm
- High Reliability
- Hermetic Package

ABSOLUTE MAXIMUM RATINGS

- Storage temperature..... -55°C to +125°C
- Case operating temperature... -40°C to +85°C
- Lead solder temperature..... 260°C, 10 seconds
- Supply Voltage..... +10 Volts

PRELIMINARY

OPERATING CONDITIONS

- Supply Voltage..... +0 to +6 Volts

OUTLINE DIMENSIONS

All dimensions are in inches (except as noted)

Pinout : 1. Emitter, 2. Base, 3. Case (Collector)

ELECTRO-OPTICAL CHARACTERISTICS (Case T = 25°C)

PARAMETER	TEST CONDITION	SYMBOL	MIN	TYP	MAX	UNIT
Collector Emitter Breakdown	$I_c = 100 \mu A, I_B = 0$	BVCEO	10			Volts
Emitter - Collector Breakdown	$I_E = 100 \mu A, I_B = 0$	BVECO	3			Volts
Collector Dark Current	VCE = 3V, H = 0 mW/cm ²	ICEO			100	nA
Collector-Emitter Saturation	$I_c = 2 \text{ mA}, I_B = 100 \mu A$	VCESAT			0.3	Volts
Response Time	10%-90%, IC = 1 mA VCE = 5 V, RL=1000 Ω	t _r		8		μsec
		t _f		8		μsec
Current Gain	IC = 1 mA, VCE = 5 V	H _{fe}	350	500		

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